P5MNC4P0

30V N-Channel MOSFETs

BV_{DSS}	$R_{DS(ON)}$	I_D
30 V	4 mΩ	85 A

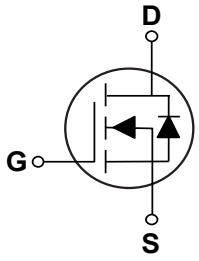
General Description

These N-Channel enhancement mode power field effect transistors are using trench technology.
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- $R_{DS(ON)} \leqq 4m\Omega @ V_{GS}=10V$
- Fast Switching
- Improved dv/dt Capability
- Green Device Available

PPAK5X6 Pin Configuration



Applications

- Battery Protection
- Load Switch
- Uninterruptible Power Supply
- MB / VGA / Vcore
- POL Applications
- SMPS 2nd SR

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current - Continuous	85	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	216	A
EAS	Single Pulse Avalanche Energy (NOTE 2)	125	mJ
IAS	Single Pulse Avalanche Current (NOTE 2)	50	A
P_D	Power Dissipation (T_C=25°C)	44.6	W
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		NC4P0	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	2.8	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	30	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=24V , V_{GS}=0V	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	2.3	4	mΩ
		V_{GS}=4.5V , I_D=10A	---	4.3	6	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=250uA	1.0	---	2.5	V
gfs	Forward Transconductance	V_{DS}=5V , I_D=30A	---	26.5	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{DS}=15V , V_{GS}=4.5V , I_D=15A	---	70	---	nC
Q_{gs}	Gate-Source Charge		---	12	---	
Q_{gd}	Gate-Drain Charge		---	17	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V , R_G=3.3Ω , I_D=15A	---	11	---	nS
T_r	Rise Time		---	120	---	
$T_{d(off)}$	Turn-Off Delay Time		---	25	---	
T_f	Fall Time		---	60	---	
C_{iss}	Input Capacitance	V_{DS}=15V , V_{GS}=0V , F=1MHz	---	3500	---	pF
C_{oss}	Output Capacitance		---	386	---	
C_{rss}	Reverse Transfer Capacitance		---	358	---	
R_g	Gate Resistance	V_{GS}=0V , V_{DS}=0V , F=1MHz	---	1.4	---	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	85	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A	---	---	1.2	V

NOTES：

1. Repetitive Rating：Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=50A.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

Characteristics Curves

FIG. 1-Continuous Drain Current vs. T_C

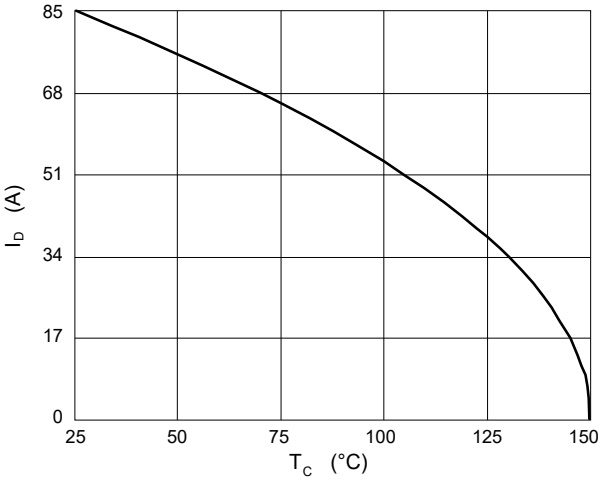


FIG. 2-Normalized $R_{DS(ON)}$ vs T_J

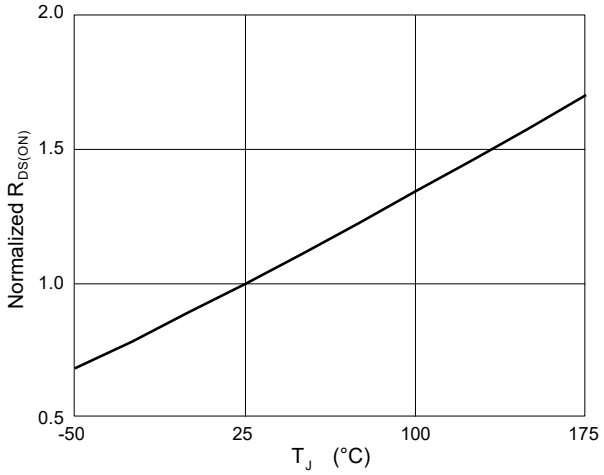


FIG. 3-Normalized V_{th} vs T_J

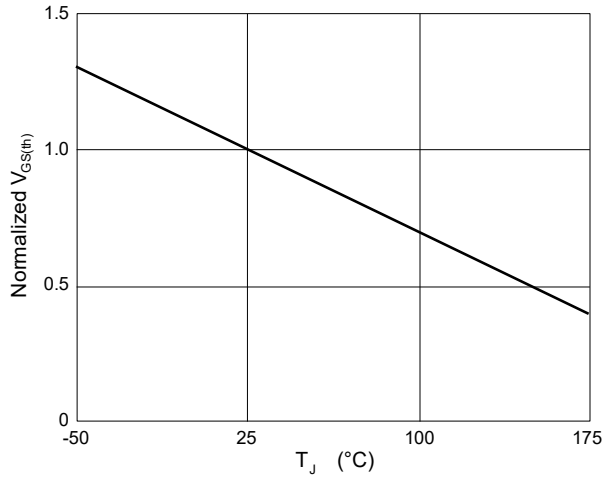


FIG. 4-Forward Characteristics of Body Diode

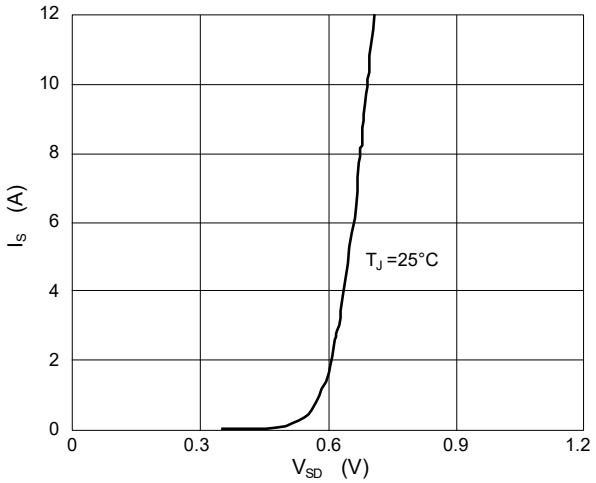


FIG. 5-Typical Output Characteristics

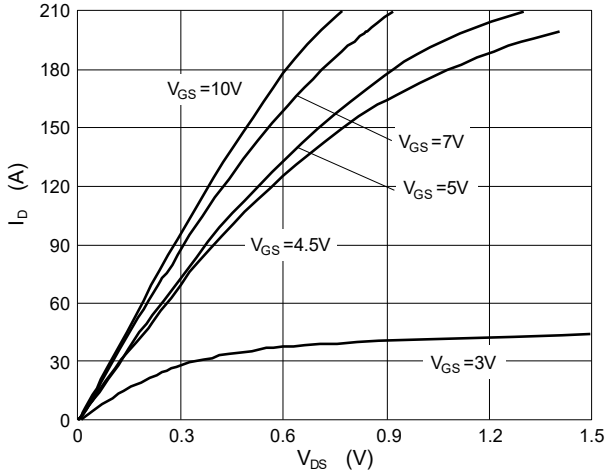
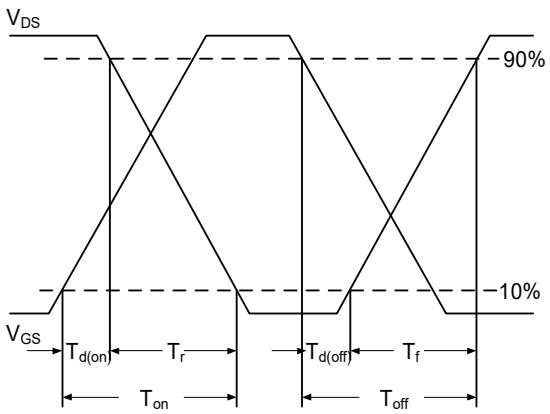
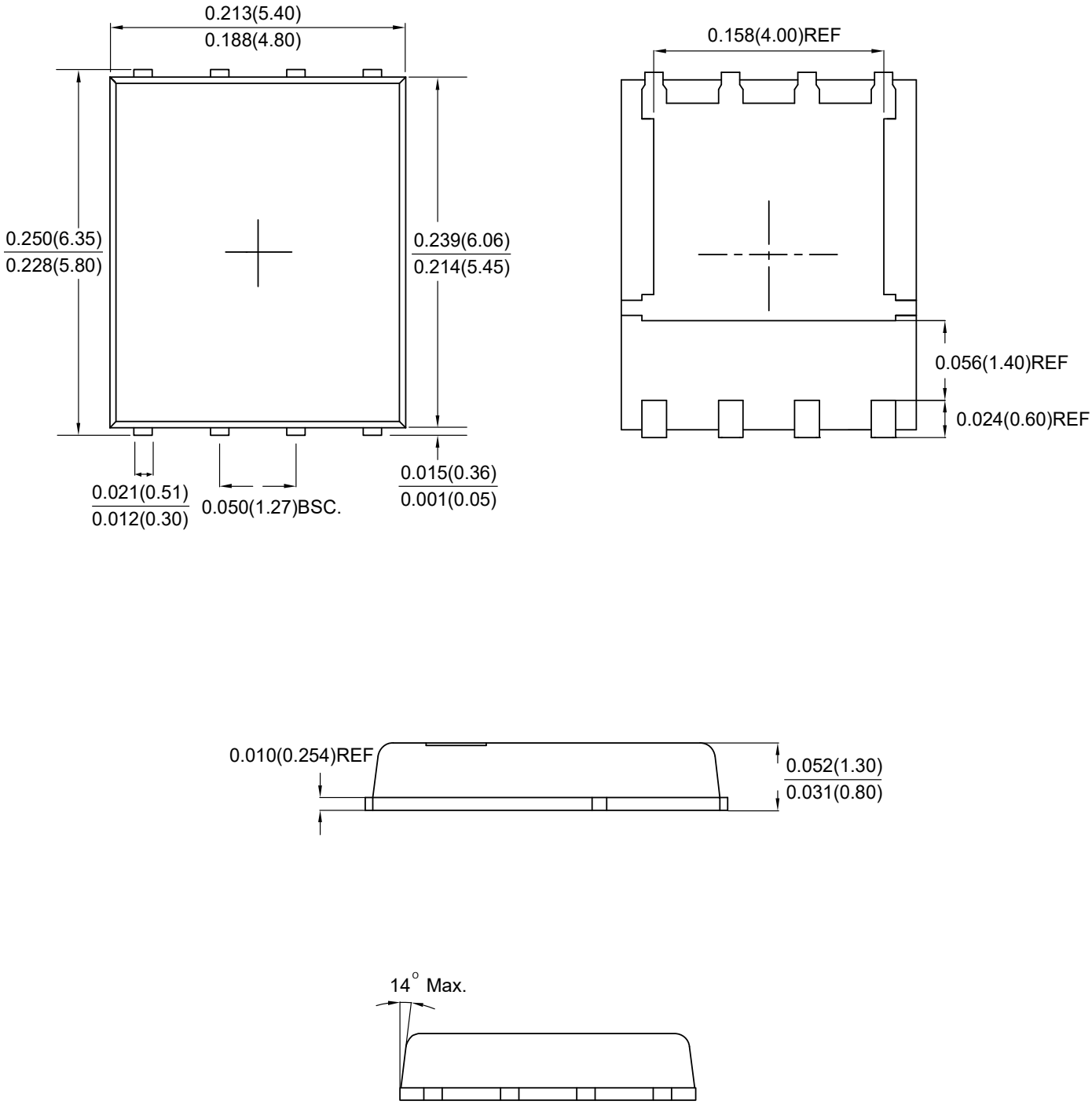


FIG. 6 - Switching Time Waveform



Package Outline Dimensions



PPAK5X6

Dimensions in inches and (millimeters)

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